





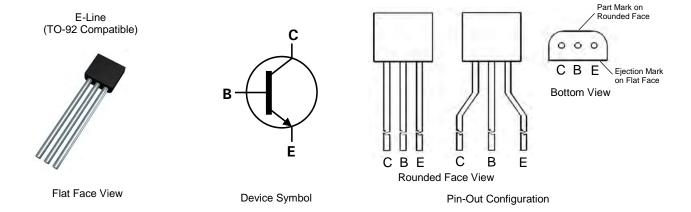
150V NPN MEDIUM POWER TRANSISTOR IN E-LINE

Features

- BV_{CEO} > 150V
- I_C = 4A High Continuous Collector Current
- I_{CM} = 10A Peak Pulse Current
- T_J up to 200°C for High Temperature Operation
- Low Saturation Voltage < 100mV @ 1A
- P_D = 1.2W Power dissipation
- Complementary NPN Type: ZTX955
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: E-Line (TO-92 Compatible)
- Case Material: molded plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.159 grams (approximate)



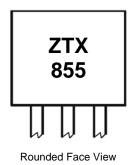
Ordering Information (Note 4)

Product	Marking	Package	Leads	Quantity
ZTX855STZ	ZTX855	E-Line	Joggled	2,000 taped per Ammo Box
ZTX855	ZTX855	E-Line	Straight	4,000 loose in a Box

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZTX855 = Product type Marking Code





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	250	V
Collector-Emitter Voltage	V _{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	4	Α
Peak Pulse Current	I _{CM}	10	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1.58	W
Power Dissipation (Note 6)	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{OJA}	150	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	110	°C/W
Thermal Resistance, Junction to Lead (Note 7)	Rejc	50	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +200	°C

ESD Ratings (Note 8)

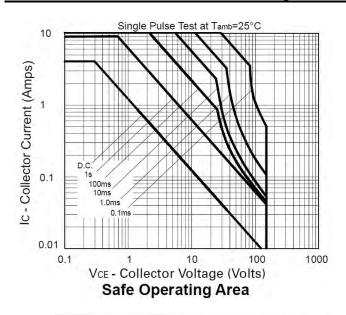
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

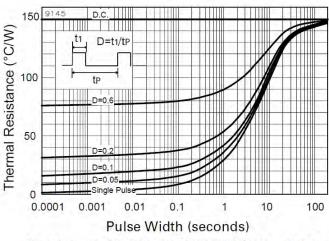
Notes:

- 5. For a through-hole device mounted at the seating plane (2.5mm lead length) with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on minimum recommended pad layout with 12mm lead length from the bottom of package to the board.
- 7. Thermal resistance from junction to solder-point at the seating plane (2.5mm from the bottom of package along the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

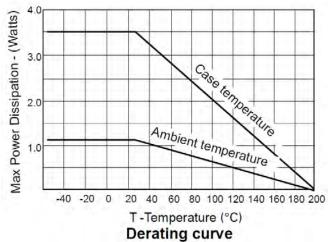


Thermal Characteristics and Derating Information





Maximum transient thermal impedance







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

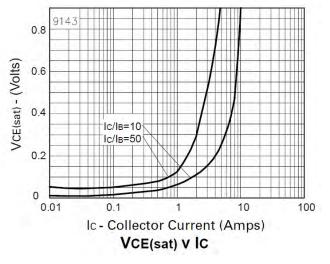
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	250	375	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	250	375	-	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	150	180	_	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	6	8	_	V	$I_{E} = 100 \mu A$
Collector-Base Cut-off Current	Ісво	_	_	50 1	nΑ μΑ	V _{CB} = 200V V _{CB} = 200V, @T _A = +100°C
Collector-Emitter Cut-off Current	l _{CER} R ≤ 1kΩ	-	_	50 1	nΑ μΑ	V _{CB} = 200V V _{CB} = 200V, @T _A = +100°C
Emitter-Base Cut-off Current	I _{EBO}	-	_	10	nA	$V_{EB} = 6V$
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(sat)}	_	20 35 60 210	40 60 100 260	mV	$I_C = 100$ mA, $I_B = 5$ mA $I_C = 500$ mA, $I_B = 50$ mA $I_C = 1$ A, $I_B = 100$ mA $I_C = 4$ A, $I_B = 400$ mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	960	1100	mV	$I_C = 4A, I_B = 400mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	880	1000	mV	$I_C = 4A$, $V_{CE} = 5V$
DC Current Gain (Note 9)	h _{FE}	100 100 35	200 200 55 10	- 300 - -		$I_C = 10$ mA, $V_{CE} = 5$ V $I_C = 1$ A, $V_{CE} = 5$ V $I_C = 4$ A, $V_{CE} = 5$ V $I_C = 10$ A, $V_{CE} = 5$ V
Current Gain-Bandwidth Product (Note 9)	f⊤	-	90	-	MHz	$V_{CE} = 10V, I_{C} = 100mA$ f = 50MHz
Output Capacitance (Note 9)	C_{obo}	-	22	-	pF	V _{CB} = 20V, f = 1MHz
Switching Times	t _{on} t _{off}	_	66 2130	=	ns ns	$I_C = 1A$, $V_{CC} = 50V$ $I_{B1} = -I_{B2} = 100mA$

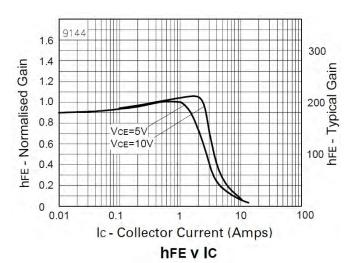
Notes: 9. Measured under pulsed conditions. Pulse width • 300µs. Duty cycle • 2%

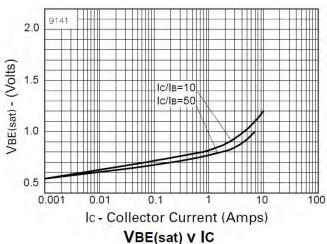
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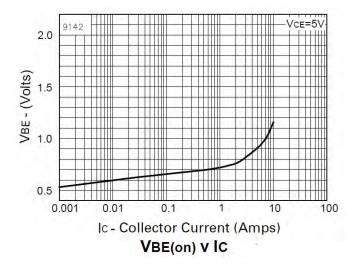


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





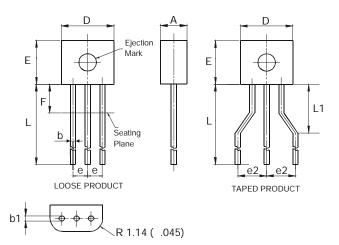






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



E-Line						
Dim	Min	Max	Тур			
Α	2.16	2.41	1			
b	0.41	0.495	-			
b1	0.41	0.495	1			
D	4.37	4.77	_			
Е	3.61	4.01	1			
е	_	_	1.27			
e2	_	_	2.54			
F	_	2.50	_			
L	13.00	13.97	_			
L1	2.50	3.50	-			
All Dimensions in mm						

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to voltage spacing between terminals.





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